Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
-20V	35mΩ @ V_{GS} = -4.5V	-6.0A
	45mΩ @ V_{GS} = -2.5V	-5.2A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- ESD Protected up to 3kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

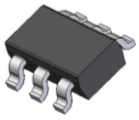
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC Converters
- Motor Control
- Power Management Functions
- Analog Switch

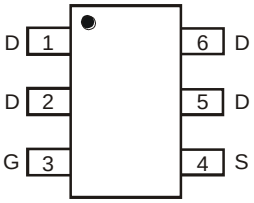
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

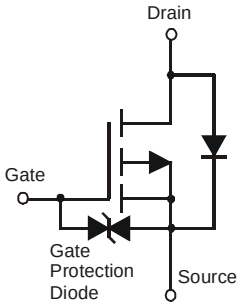
ESD PROTECTED TO 3kV



Top View



Top View
Pin-Out



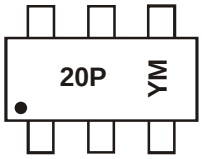
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2035UVT-7	TSOT26	3,000/Tape & Reel
DMP2035UVT-13	TSOT26	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



20P = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: Y = 2011)
M = Month (ex: 9 = September)

Date Code Key

Year	2011	~	2016	2017	2018	2019	2020	2021	2022
Code	Y	~	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-6.0 -4.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-7.2 -5.7	A
Continuous Drain Current (Note 6) V_{GS} = -2.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-5.2 -4.1	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-6.2 -4.9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-2.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-24	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	106	°C/W
	t<10s		74	
Total Power Dissipation (Note 6)		P_D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	65	°C/W
	t<10s		46	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	11.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	-0.7	-1.5	V	V_{DS} = V_{GS}, I_D = -250µA
Gate Threshold Voltage Temperature Coefficient	$\triangle V_{GS(TH)}/\triangle T_J$	—	2.5	—	mV/°C	I_D = -250µA ,Referenced to +25°C
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	23	35	mΩ	V_{GS} = -4.5V, I_D = -4.0A
		—	30	45		V_{GS} = -2.5V, I_D = -4.0A
		—	41	62		V_{GS} = -1.8V, I_D = -2.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	18	—	S	V_{DS} = -5V, I_D = -5.5A
Diode Forward Voltage (Note 6)	V_{SD}	—	-0.7	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1,610	2,400	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	157	210		
Reverse Transfer Capacitance	C_{rss}	—	145	200		
Gate Resistance	R_G	—	9.4	14.1	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	15.4	23.1	nC	V_{DS} = -10V, V_{GS} = -4.5V I_D = -4A
Gate-Source Charge	Q_{gs}	—	2.5	—		
Gate-Drain Charge	Q_{gd}	—	3.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	17	33	ns	V_{GS} = -4.5V, V_{DS} = -10V, R_G = 6Ω, I_D = -1A, R_L = 10Ω
Turn-On Rise Time	t_R	—	12	19		
Turn-Off Delay Time	$t_{D(OFF)}$	—	94	150		
Turn-Off Fall Time	t_F	—	42	64		
Reverse Recovery Time	t_{RR}	—	14	25	ns	I_F =-4.5A, di/dt=100A/µS
Reverse Recovery Charge	Q_{RR}	—	4	8	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

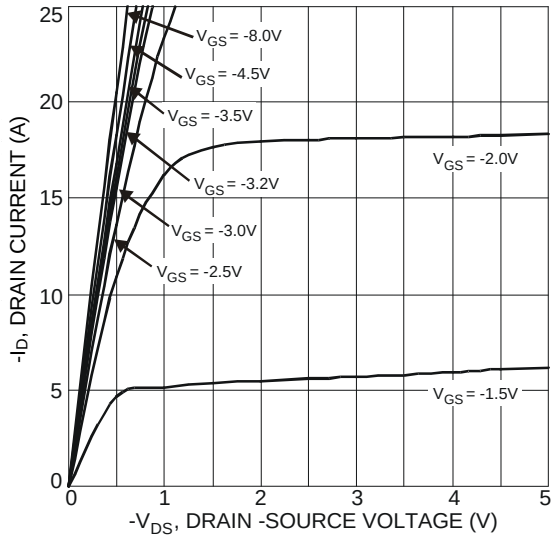


Fig. 1 Typical Output Characteristics

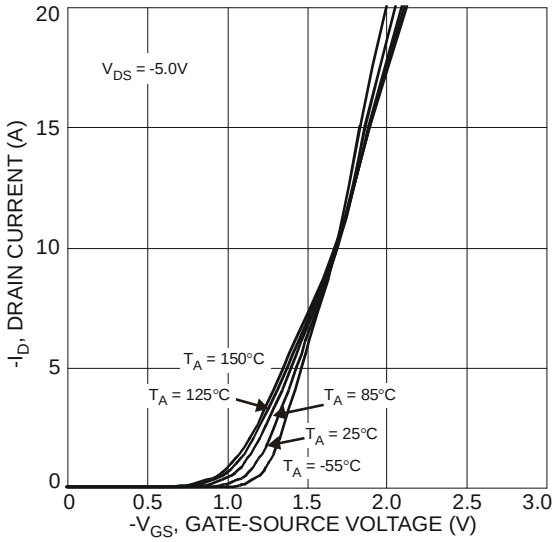


Fig. 2 Typical Transfer Characteristics

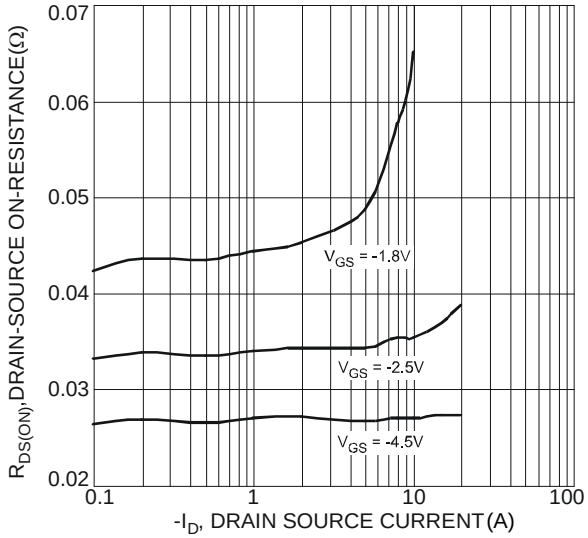


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

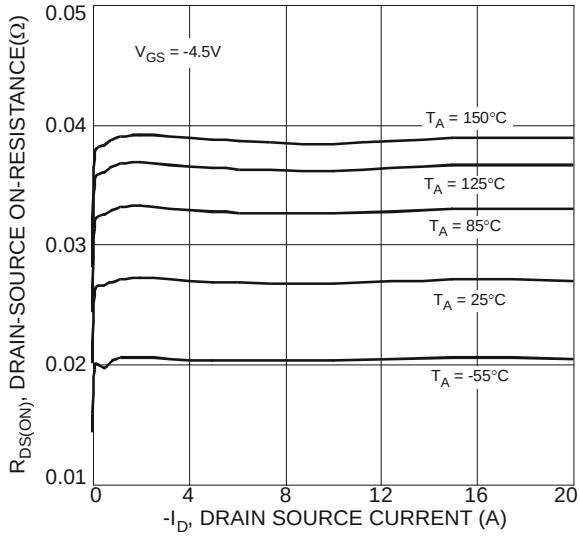


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

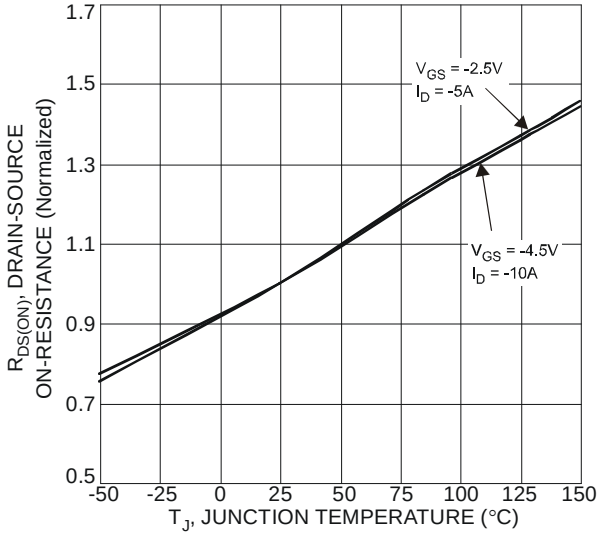


Fig. 5 On-Resistance Variation with Temperature

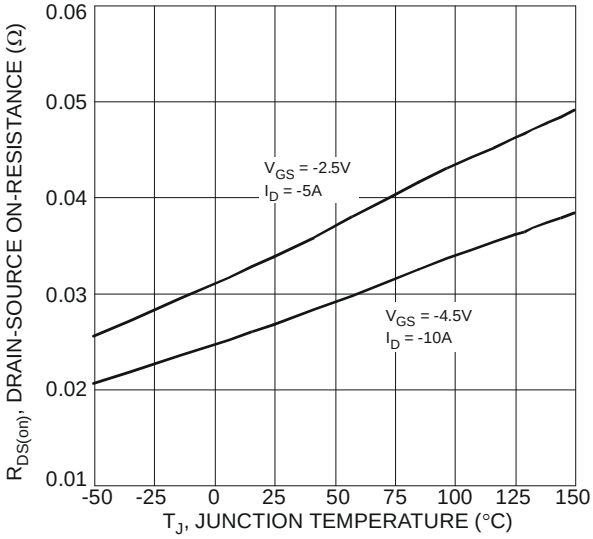


Fig. 6 On-Resistance Variation with Temperature

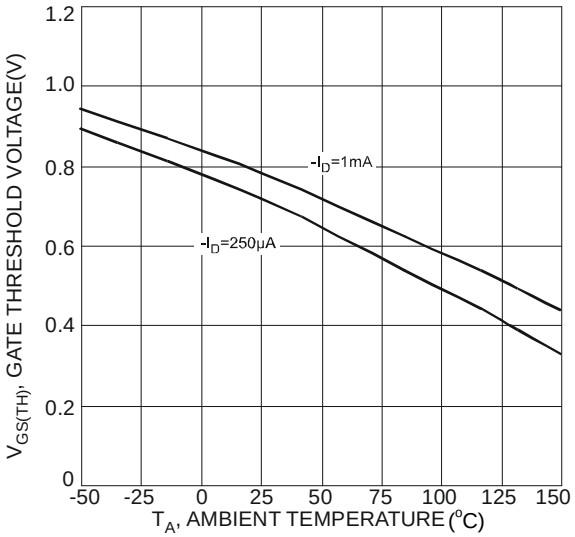


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

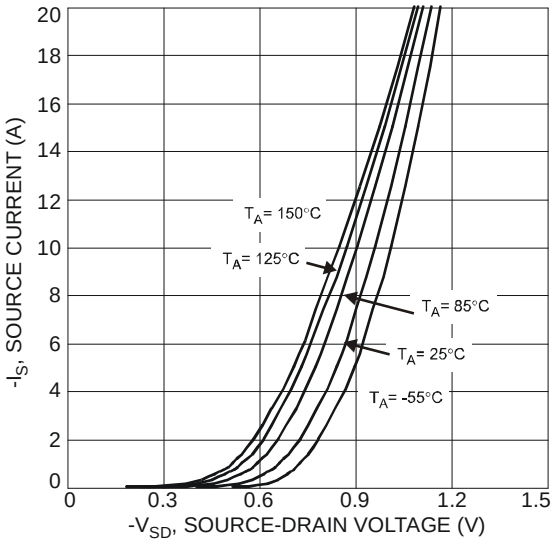


Fig. 8 Diode Forward Voltage vs. Current

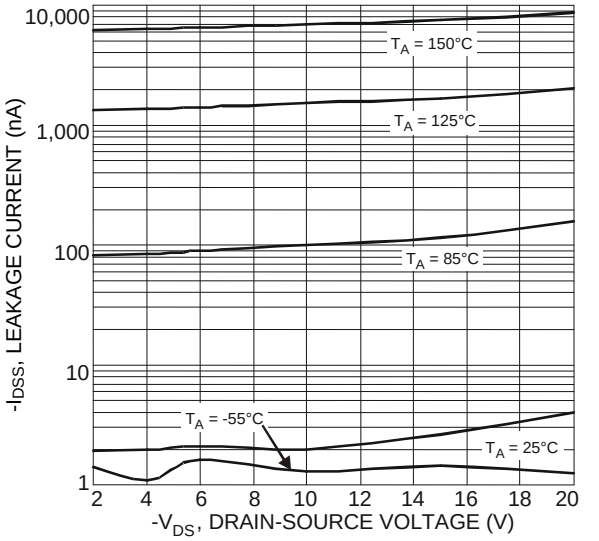


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

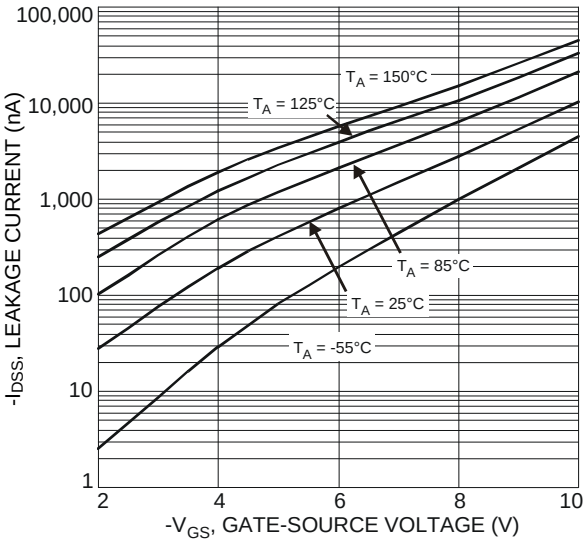


Fig. 10 Typical Gate-Source Leakage Current vs. Voltage

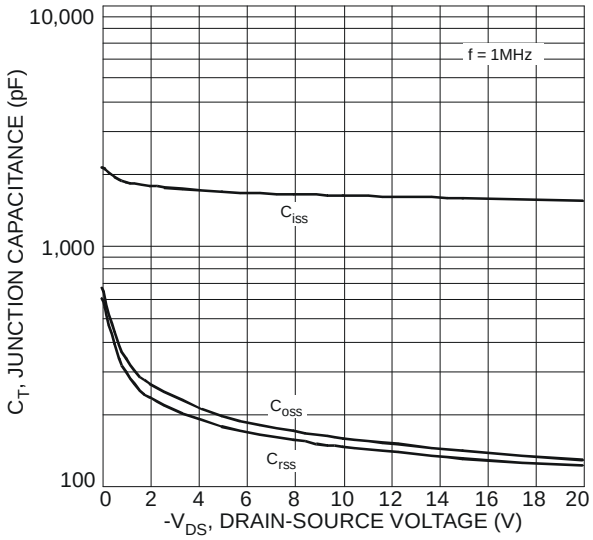


Fig. 11 Typical Junction Capacitance

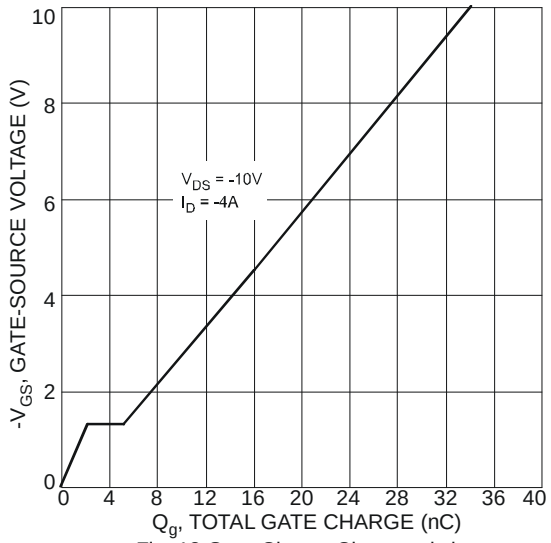


Fig. 12 Gate-Charge Characteristics

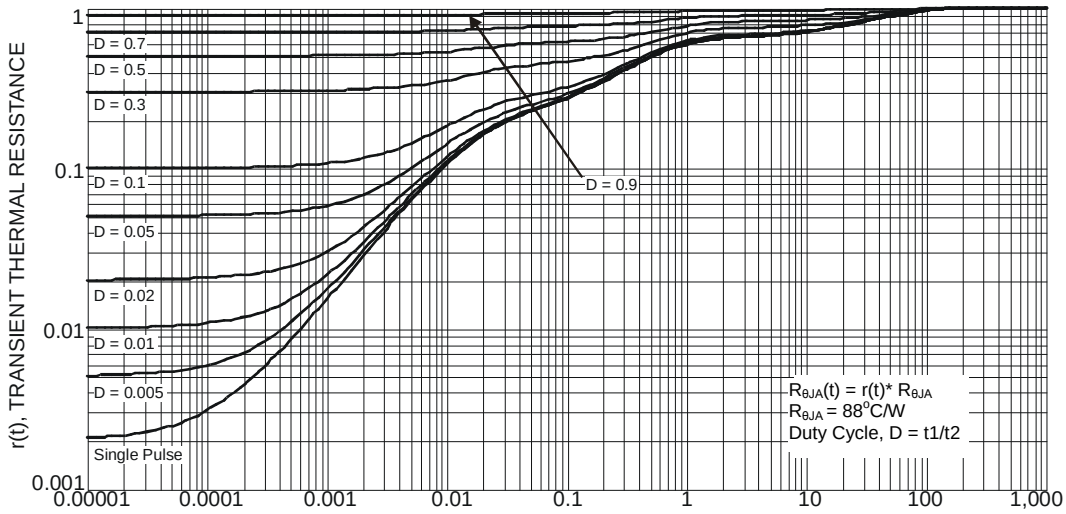
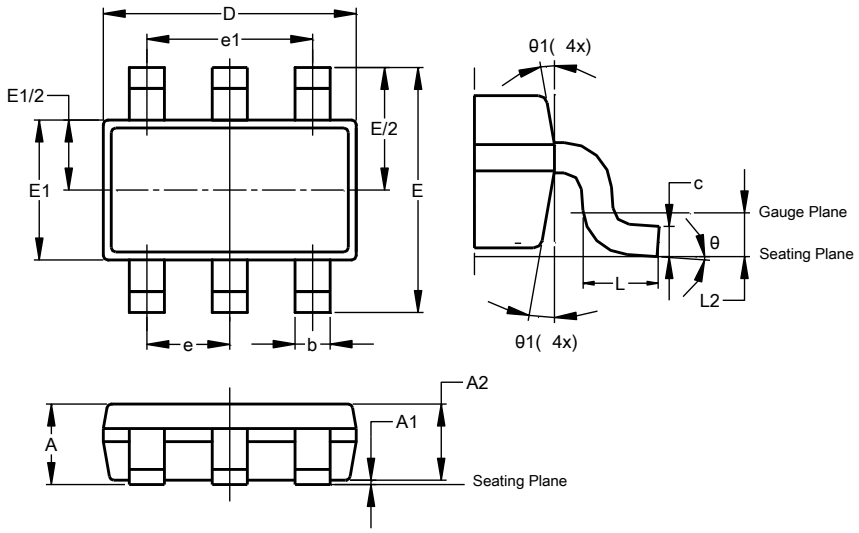


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

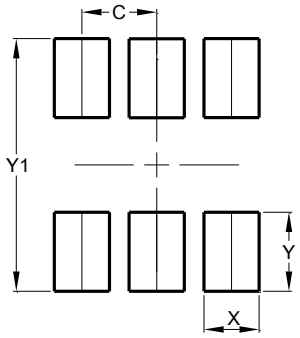


TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Diodes Incorporated:

DMP2035UVT-7